32,768 WORD x 8 Bit CMOS Static RAM (Industrial Temperature Range Operation)

FEATURES

- **Industrial Temperature Range : -40 to 85° C**
- **Fast Access Time: 70, 100ns(max.)**
- **Low Power Dissipation**
  Standby (CMOS) : 275μW(max.)
  Operating : 110mW(max.)
- **Single 5V±10% power supply**
- **TTL compatible inputs and outputs**
- **Fully Static Operation**
  - No clock or refresh required
- **Three State Output**
- **Low Data Retention Voltage: 2V(Min.)**
- **Jedec Standard Pin Configuration**
  KM62256BLPI : 28-DIP-600B
  KM62256BLGI : 28-SOP-450

GENERAL DESCRIPTION

The KM62256BLI/BLI-L is a 262,144-bit high speed Static Random Access Memory organized as 32,768 words by 8 bits.
The device is fabricated using Samsung's advanced CMOS technology.
The KM62256BLI/BLI-L has been designed for high speed and low power applications. It is particularly well suited for battery back-up memory application.
And -40 to 85° C operating temperature range makes it ideal for industrial use.

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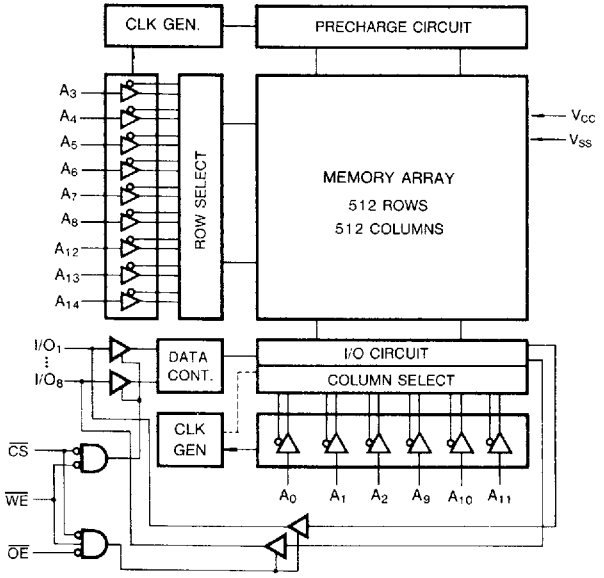
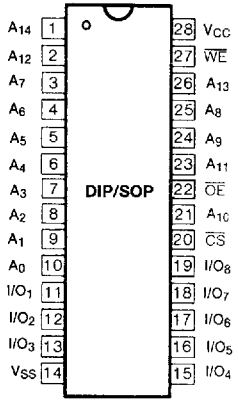
FUNCTIONAL BLOCK DIAGRAM



PIN CONFIGURATION (Top Views)



Pin Name	Pin Function
A0-A14	Address Inputs
WE	Write Enable
CS	Chip Select I
OE	Output Enable
I/O1~I/O8	Data Inputs/Outputs
Vcc	Power(+5V)
Vss	Ground

SAMSUNG ELECTRONICS

ABSOLUTE MAXIMUM RATINGS*

Item	Symbol	Rating	Unit
Voltage on Any Pin Relative to Vss	V_{IN}, V_{OUT}	-0.5 to 7.0	V
Voltage on Vcc Supply Relative to Vss	V_{CC}	-0.5 to 7.0	V
Power Dissipation	P_D	1.0	W
Storage Temperature	T_{STG}	-65 to + 150	°C
Operating Temperature	T_A	-40 to 85	°C
Soldering Temperature and Time	T_{SOLDER}	260°C, 10sec(Lead only)	—

* Stresses greater than those listed under "ABSOLUTE MAXIMUM RATINGS" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operating sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

RECOMMENDED OPERATING CONDITIONS (T_A=-40 to 85°C)

Item	Symbol	Min	Typ	Max	Unit
Supply Voltage	V_{CC}	4.5	5.0	5.5	V
Ground	V_{SS}	0	0	0	V
Input High Voltage	V_{IH}	2.2	—	V_{CC}+0.5	V
Input Low Voltage	V_{IL}	-0.5	—	0.8	V

* V_{IL}(min.)=-3.0V for$\leq$50ns pulse

DC AND OPERATING CHARACTERISTICS

(T_A=-40 to 85°C, V_{CC}=5V$\pm$10%, unless otherwise specified)

Item	Symbol	Test Condition		Min	Typ*	Max	Unit
Input Leakage Current	I_{LI}	V_{IN}=Vss to V_{CC}		-1		1	μA
Output Leakage Current	I_{LO}	$\overline{CS}$=V_{IN} or $\overline{OE}$=V_{IH} or $\overline{WE}$=V_{IL}, $V_{I/O}$=Vss to V_{CC}		-1		1	μA
Operating Power Supply Current	I_{CC}	$\overline{CS}$=V_{IL}, V_{IN}=V_{IH} or V_{IL} II/O=0mA			7	20	mA
Average Operating Current	I_{CC1}	Cycle Time=1μs, $\overline{CS}\leq$0.2V, $V_{IL}\leq$0.2V $V_{IH}\geq V_{CC}$-0.2V, $I_{I/O}$=0mA				10	mA
	I_{CC2}	$\overline{CS}$=V_{IL}, Min Cycle,100% Duty $I_{I/O}$=0mA				70	mA
Standby Power Supply Current	I_{SB}	$\overline{CS}$=V_{IH}				2	mA
	I_{SB1}	$\overline{CS}\geq V_{CC}$-0.2V $V_{IN}\geq V_{CC}$-0.2V or $V_{IN}\leq$0.2V	L-Ver			100	μA
			LL-Ver			20	μA
Output Low Voltage	V_{OL}	I_{OL}=2.1mA				0.4	V
Output High Voltage	V_{OH}	I_{OH}=-1.0mA		2.2			V

* Typ : V_{CC}=5V, T_A=25°C

CAPACITANCE (f=1MHz, T_A=25°C)

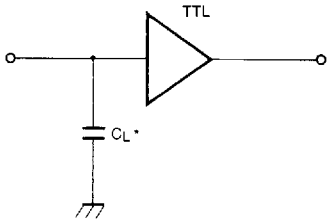
Item	Symbol	Test Condition	Min	Max	Unit
Input Capacitance	C_{IN}	V_{IN}=0V	-	6	pF
Input/Output Capacitance	$C_{I/O}$	$V_{I/O}$=0V	-	8	pF

* Note : Capacitance is sampled and not 100% tested.

TEST CONDITIONS (T_A=-40 to 85°C, V_{CC}=5V±10%, unless otherwise specified)

Parameter	Value
Input Pulse Level	0.8 to 2.4V
Input Rise and Fall Time	5 ns
Input and Output Timing Reference Levels	1.5 V
Output Load	C_L=100pF+1TTL Load

TEST CIRCUIT



* Including Scope and Jig Capacitance

READ CYCLE

Parameter	Symbol	KM62256BLI-7 KM62256BLGI-7		KM62256BLI-10 KM62256BLGI-10		Unit
		Min	Max	Min	Max	
Read Cycle Time	t_{RC}	70		100		ns
Address Access Time	t_{AA}		70		100	ns
Chip Select to Output	t_{CO}		70		100	ns
Output Enable to Valid Output	t_{OE}		35		50	ns
Chip Select to Low-Z Output	t_{LZ}	10		10		ns
Output Enable to Low-Z Output	t_{OLZ}	5		5		ns
Chip Deselect to High-Z Output	t_{HZ}	0	30	0	35	ns
Output Disable to High-Z Output	t_{OHZ}	0	30	0	35	ns
Output Hold from Address Change	t_{OH}	5		10		ns

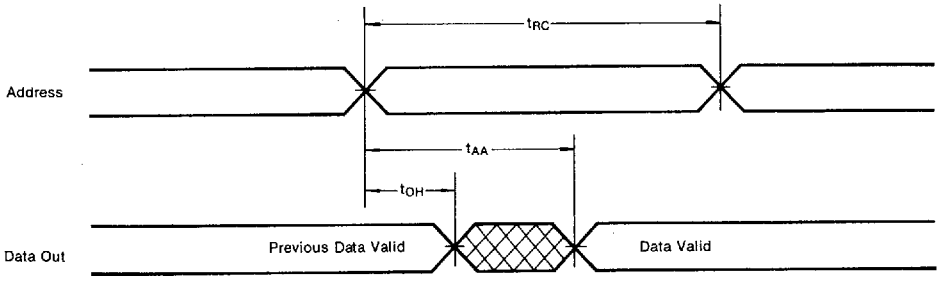
WRITE CYCLE

Parameter	Symbol	KM62256BLI-7 KM62256BLGI-7		KM62256BLI-10 KM62256BLGI-10		Unit
		Min	Max	Min	Max	
Write Cycle Time	t_{WC}	70		100		ns
Chip Select to End of Write	t_{CW}	60		80		ns
Address Set-up Time	t_{AS}	0		0		ns
Address Valid to End of Write	t_{AW}	60		80		ns
Write Pulse Width	t_{WP}	50		60		ns
Write Recovery Time	t_{WR}	0		0		ns
Write to Output High-Z	t_{WHZ}	0	25	0	35	ns
Data to Write Time Overlap	t_{DW}	30		50		ns
Data Hold from Write Time	t_{DH}	0		0		ns
End Write to Output Low-Z	t_{OW}	5		10		ns

TIMING DIAGRAMS

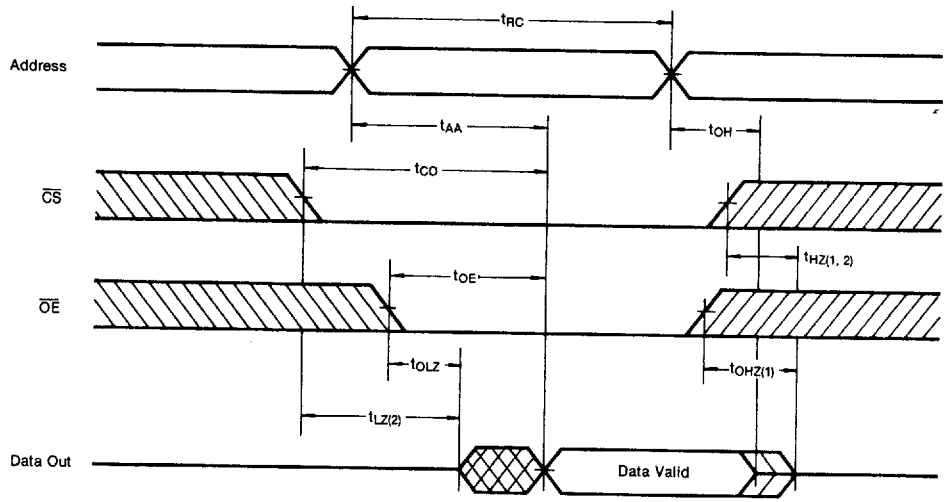
TIMING WAVEFORM OF READ CYCLE (Address Controlled)

($\overline{CS}$=$\overline{OE}$, V_{IL}, $\overline{WE}$=V_{IH})



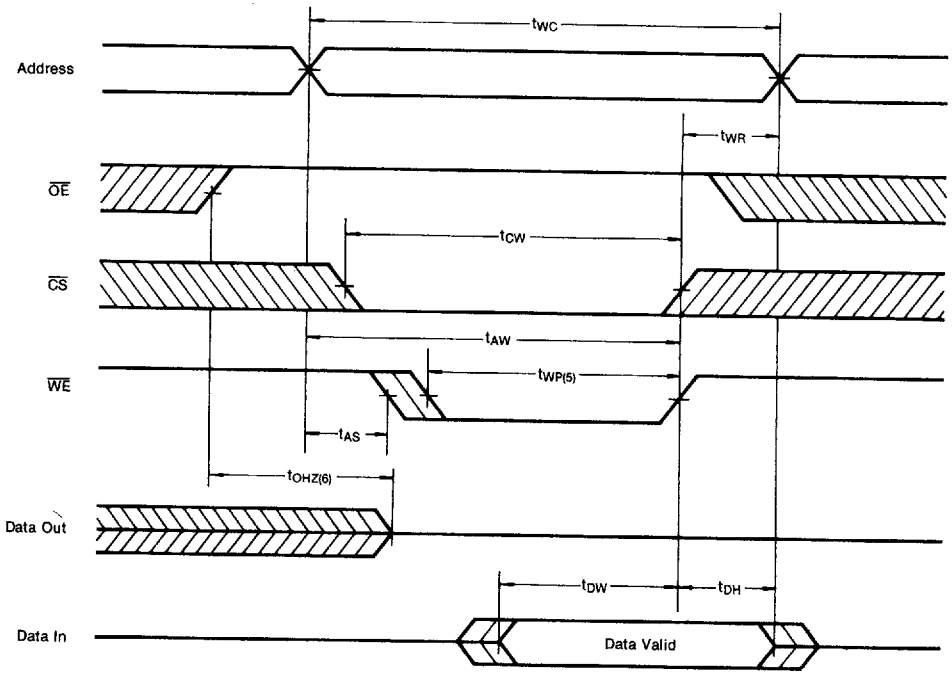
TIMING WAVEFORM OF READ CYCLE (2)

($\overline{WE}$ = V_{IH}) (Note 1, 2, 3, 4)



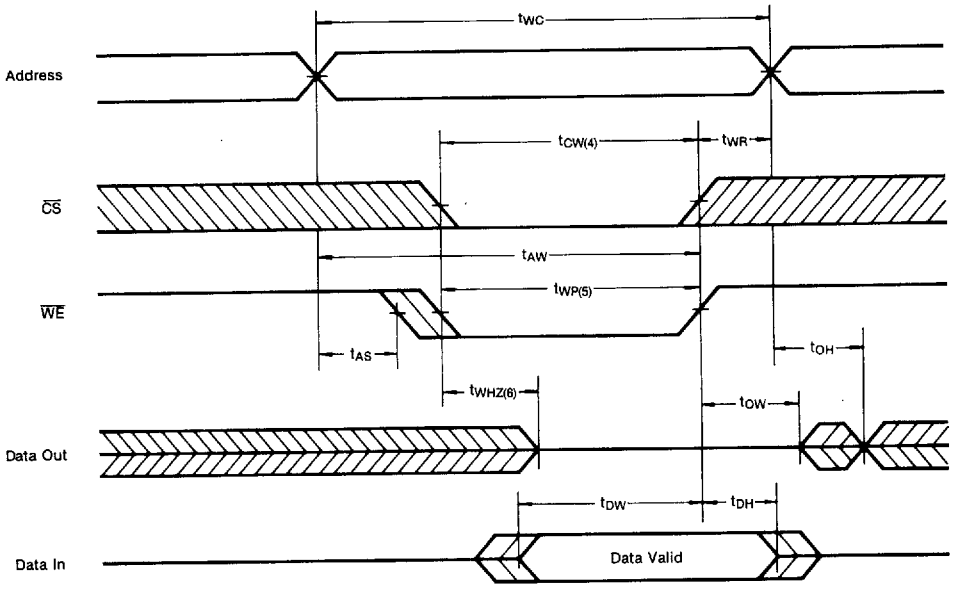
TIMING WAVEFORM OF WRITE CYCLE (3)

($\overline{OE}$ Clocked) (Note 5, 6, 7, 8)



TIMING WAVEFORM OF WRITE CYCLE (4)

($\overline{OE}$ Low Fixed) (Note 5, 6, 7, 8, 9)



Notes

1. t_{HZ} and t_{OHZ} are defined as the time at which the outputs achieve the open circuit condition and are not referenced to the V_{OH} or V_{OL} level.
2. At any given temperature and voltage condition t_{HZ} (max.) is less than t_{LZ} (min.) both for a given device and from device to device.
3. $\overline{WE}$ is high for read cycle.
4. Address valid prior to or coincident with $\overline{CS}$ transition Low.
5. A write occurs during the overlap (t_{WP}) of a low $\overline{CS}$ and WE.
6. During this period, I/O pins are in the output state. The input signals out of phase must not applied.
7. $\overline{CS}$ or $\overline{WE}$ must be high during address transition state.
8. If $\overline{OE}$ is high, I/O pins remain in a high-impedance state.
9. $\overline{OE}$ is continuously low ($\overline{OE} = V_{IL}$).

FUNCTIONAL DESCRIPTION

$\overline{CS}$	$\overline{WE}$	$\overline{OE}$	Mode	I/O Pin	Vcc Current
H	X*	X	Power down	High-Z	I_{SB}, I_{SB1}
L	H	H	Output disable	High-Z	I_{CC}
L	H	L	Read	D_{OUT}	I_{CC}
L	L	X	Write	D_{IN}	I_{CC}

* X means Don't Care

DATA RETENTION CHARACTERISTICS (T_A=-40 to 85°C)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
Vcc for Data Retention	V_{DR}	$\overline{CS}1 \geq V_{CC}-0.2V$		2.0		5.5	V
Data Retention Current	I_{DR}	$V_{CC} \geq 3.0V$	L	-		50	μA
		$\overline{CS} \geq V_{CC}-0.2V$	LL	-		10	μA
Data Retention Set-up Time	t_{SDR}	See Data Retention		0			ns
Recovery Time	t_{RDR}	Waveforms(below)		t_{RC}*			ns

* Read Cycle Time